Preferred Device

General Purpose Transistor

NPN Silicon

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	200	mAdc
Collector Current - Peak (Note 3)	I _{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

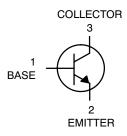
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code

M = Date Code* ■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT3904LT1	SOT-23	3000 / Tape & Reel
MMBT3904LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT3904LT3	SOT-23	10,000/Tape & Reel
MMBT3904LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

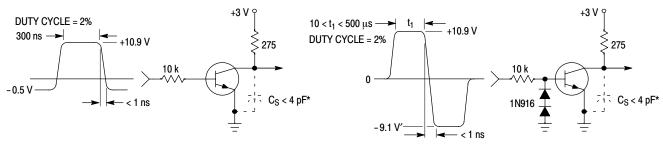
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure. BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Char	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS		1	1		ı	
Collector - Emitter Breakdown Voltage (I	V _{(BR)CEO}	40	-	Vdc		
Collector - Base Breakdown Voltage (I _C	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc	
Emitter - Base Breakdown Voltage (I _E =	10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc	
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EE}	₃ = 3.0 Vdc)	I _{BL}	-	50	nAdc	
Collector Cutoff Current (V _{CE} = 30 Vdc,	V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc	
ON CHARACTERISTICS (Note 4)						
	H _{FE}	40 70 100 60 30	- 300 - -	-		
	V _{CE(sat)}		0.2 0.3	Vdc		
$\begin{aligned} \text{Base-Emitter Saturation Voltage} \\ \text{(I}_{\text{C}} &= 10 \text{ mAdc, I}_{\text{B}} = 1.0 \text{ mAdc)} \\ \text{(I}_{\text{C}} &= 50 \text{ mAdc, I}_{\text{B}} = 5.0 \text{ mAdc)} \end{aligned}$	V _{BE(sat)}	0.65	0.85 0.95	Vdc		
SMALL-SIGNAL CHARACTERISTICS		•				
Current - Gain - Bandwidth Product (I _C	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz	
Output Capacitance (V _{CB} = 5.0 Vdc, I _E :	= 0, f = 1.0 MHz)	C _{obo}	-	4.0	pF	
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} =$	0, f = 1.0 MHz)	C _{ibo}	-	8.0	pF	
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.	0 mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio (V _{CE} = 10 Vdc,	h _{re}	0.5	8.0	X 10 ⁻⁴		
Small - Signal Current Gain (V _{CE} = 10 V	h _{fe}	100	400	-		
Output Admittance (V _{CE} = 10 Vdc, I _C =	h _{oe}	1.0	40	μmhos		
Noise Figure (V_{CE} = 5.0 Vdc, I_{C} = 100 μ	NF	-	5.0	dB		
SWITCHING CHARACTERISTICS		•				
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	-	35		
Rise Time	$I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$	t _r	-	35	ns	
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	ns	
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc}$	t _f	-	50	113	

^{4.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



^{*} Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

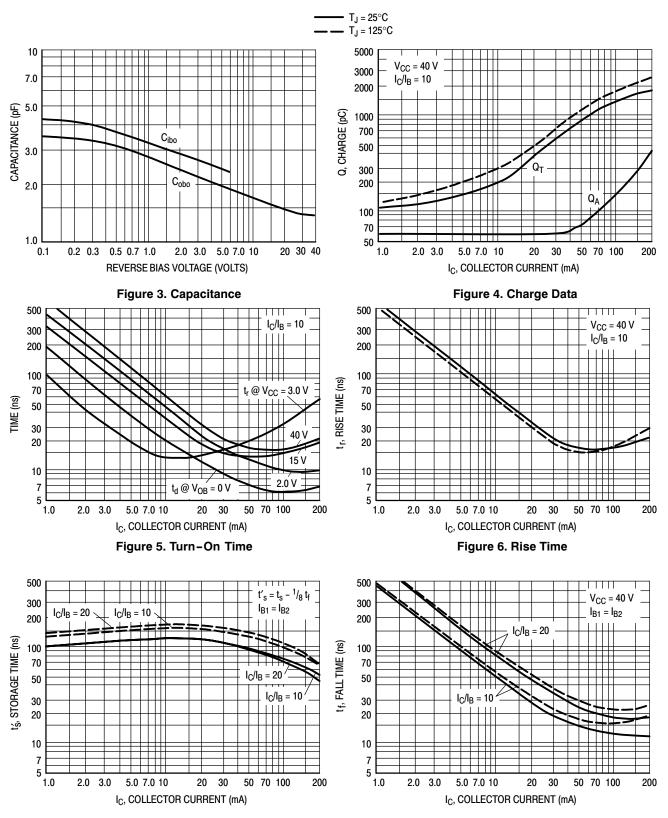
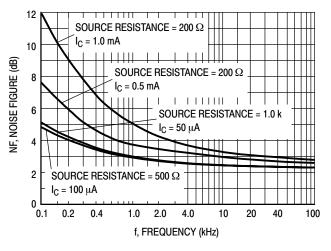


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



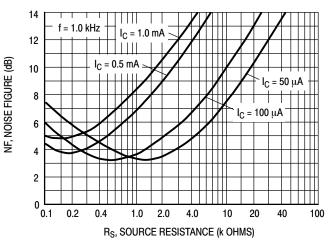
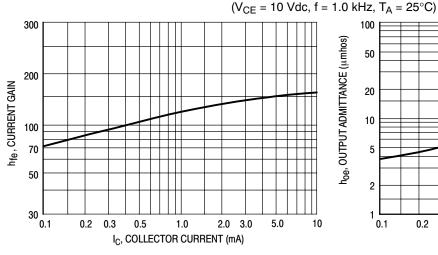


Figure 9.

Figure 10.

h PARAMETERS



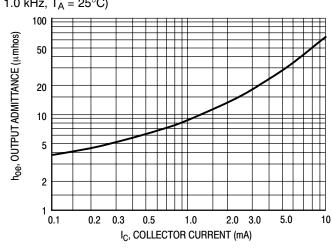


Figure 12. Output Admittance

Figure 11. Current Gain

20

10

2.0

1.0

0.5

0.2

0.1

0.2

h_{ie}, INPUT IMPEDANCE (k OHMS)

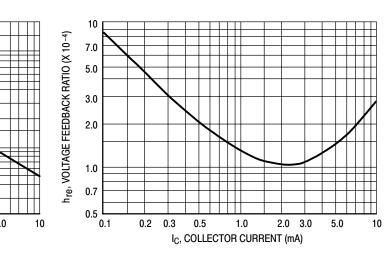


Figure 13. Input Impedance

IC, COLLECTOR CURRENT (mA)

1.0

2.0 3.0

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

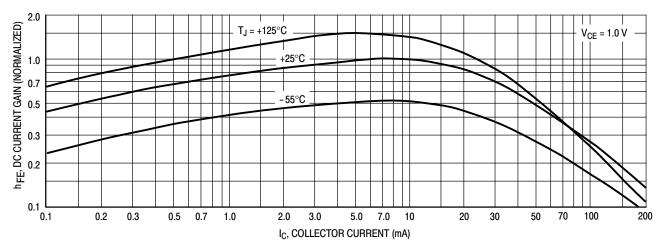


Figure 15. DC Current Gain

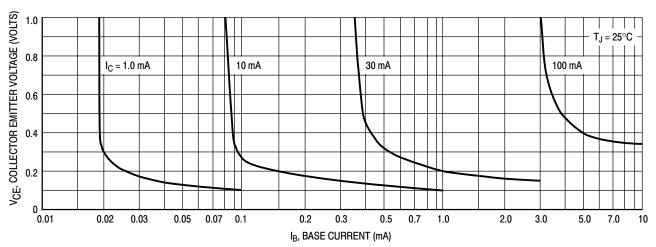


Figure 16. Collector Saturation Region

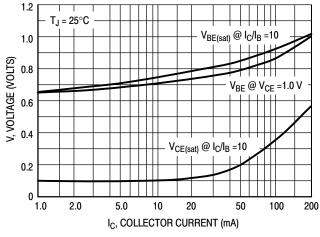


Figure 17. "ON" Voltages

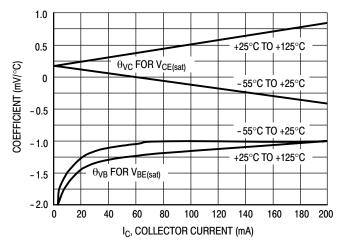


Figure 18. Temperature Coefficients

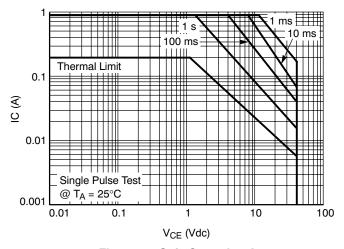
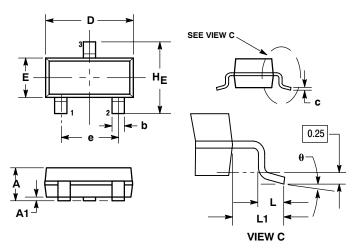


Figure 19. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN



- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW
- STANDARD 318-08

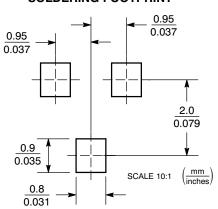
	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2 10	2 40	2 64	0.083	0.094	0 104

STYLE 6: PIN 1. BASE

2. 3. **EMITTER**

COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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